

General Description

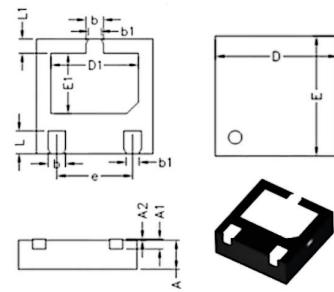
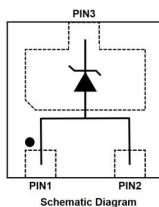
The **GS24VH20UDN** is designed to protect voltage sensitive components from damage or latch-up due to surge current. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to surge current protection for board level. Because of its small size and bi-directional design, it is ideal for use in cellular phones and portable applications that require audio line protection.

Specification Features

- Small Body Outline Dimensions: nom 0.078" x 0.078" (2.0x2.0 mm)
- Low Clamping Voltage: $V_c = 40V$ @ $I_{PP} = 200A$
- Reverse Working (Stand-off) Voltage: 24.0 V
- Low Leakage
- Response Time is Typically < 1 ns

Application

- Mobile Internet Devices (MID) and portable devices
- Personal digital assistants (PDA's)
- Cellular handsets and accessories



DFN2020-3L

	Millimeters			Inches		
	Min. (mm)	Typ. (mm)	Max. (mm)	Min. (mm)	Typ. (mm)	Max. (mm)
D	1.95	2.00	2.05	0.076	0.078	0.080
E	1.95	2.00	2.05	0.076	0.078	0.080
D1	1.45	1.50	1.55	0.057	0.059	0.061
E1	1.00	1.05	1.10	0.039	0.041	0.043
L1	0.20	0.25	0.30	0.007	0.009	0.011
L	0.35	0.40	0.45	0.013	0.015	0.017
b1	0.22REF			0.025bsc		
b	0.25	0.30	0.35	0.009	0.011	0.013
e	1.30REF					
A1	0.150REF			0.005REF		
A2	0.00	0.02	0.05	0.000	-	0.001
A	0.45	0.50	0.55	0.017	0.019	0.021

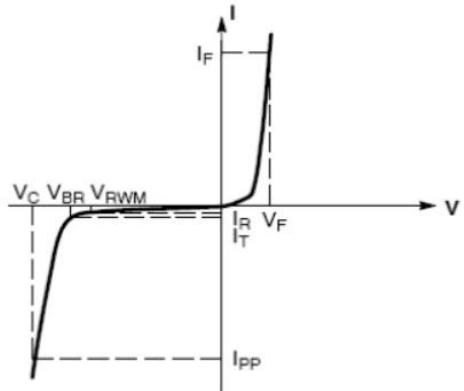
Absolute Maximum Rating

Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD) Contact		±30	kV
Peak Power Per 8 x 20μs Waveform	P_{PK}	8000	W
Junction Temperature Range	T_J	-55 to +125	°C
Storage Temperature Range	T_{stg}	-55 to +150	°C
Lead Solder Temperature – Maximum (10 Second Duration)	T_L	260	°C

GS24VH20UDN

Characteristics($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
I_T	Test Current
V_{BR}	Breakdown Voltage @ I_T
P_{PK}	Peak Power Dissipation
C	Max. Capacitance @ $V_R = 0$ and freq.=1 MHz



Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Reverse Stand-off Voltage	V_{RWM}				24	V
Diode Forward Voltage	V_F	$I_F=10\text{mA}$		0.8	1.2	V
Reverse Breakdown Voltage	V_{BR}	$I_T=1\text{mA}$	25.0		29.0	V
Reverse Leakage Current	I_R	$V_{RWM}=24\text{V}$			1.0	uA
Clamping Voltage	V_C	$I_{PP}=200\text{A}$ tp=8/20us		33	40	V
Junction Capacitance	C_J	$V_R=0\text{V}$, f = 1MHz	700		850	pF